TSMC-03-294

April 16, 2004

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
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Subject: Serial No. 10/786,798 02/25/04

Kuo-Chi Tu et al.

SPACER PROCESS TO PREVENT THE REVERSE TUNNELING IN SPLIT GATE FLASH

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on April 22, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date 4/26/04

U.S. Patent 6,400,603 to Blyth et al., "ELectronically-Eraseable Programmable Read-Only Memory Having Reduced-Page-Size Program and Erase," discusses an array of FLASH electrically eraseable programmable read-only memory cells having reduced-page-size erasing and programming.

U.S. Patent 6,617,638 to Chiang et al., "Tapered Floating Gate with Nitride Spacers to Prevent Reverse Tunneling During Programming in a Split Gate Flash," discloses a method of forming a split-gate flash memory cell with a tapered floating gate.

U.S. Patent 6,465,841 to Hsieh et al., "Split Gate Flash Memory Device Having Nitride Spacer to Prevent Inter-poly Oxide Damage," teaches a method to fabricate a split-gate flash memory cell with nitride spacers.

U.S. Patent 6,380,030 to Chen et al., "Implant Method for Forming Si3N4 Spacer," discloses an implant method for forming a silicon nitride spacer.

U.S. Patent 6,031,264 to Chien et al., "Nitride Spacer Technology for Flash EPROM," discloses a nitride spacer for flash EPROM.

Sincerely,

Stephen B. Ackerman, Reg. #37761

Sheet 1 of 1

Form PTO-1449

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

Docket Number (Optional)	Application Number
TSMC-03-294	10/786,798
Applicant: Kuo-Chi Tu et al.	
Filing Date: 02/25/04	Group Art Unit

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	6400603	6/4/02	Blyth et al.	365	185.12	5/3/00
	6617638	9/9/03	Chiang et al.	257	316	1/8/01
	6465841	10/15/02	Hsieh et al.	257	321	11/13/00
	6380030	4/30/02	Chen et al.	438	257	4/23/99
	6031264	2/29/00	Chien et al.	257	315	2/25/99

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES	Translation NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER	DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.